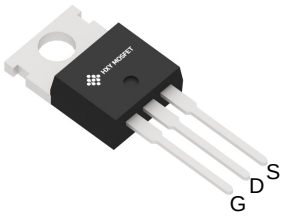
Description

The SQP120N10-09_GE3 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable.



TO-220C

General Features

V_{DS} = 100V I_D = 70A

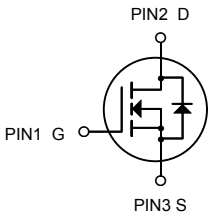
$R_{DS(ON)}$ < 10.5mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SQP120N10-09_GE3	TO-220C	HXY MOSFET	50

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current@Tc=25°C	70	A
I_{DM}	Puled Drain Current [1]	280	A
EAS	Single Pulse Avalanche Energy [3]	110	mJ
P_D@T_C=25°C	Total Power Dissipation [4]	100	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	64	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Ambient [1]	1.25	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I_D=1mA	---	0.098	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	8.5	10.5	mΩ
		V_{GS}=4.5V , I_D=15A	---	9.5	15	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.57	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25°C	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55°C	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.48	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=50V , V_{GS}=50V , I_D=10A	---	31.3	---	nC
Q_{gs}	Gate-Source Charge		---	3.49	---	
Q_{gd}	Gate-Drain Charge		---	7.63	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=4Ω I_D=10A	---	16	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	40	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	1368	---	pF
C_{oss}	Output Capacitance		---	451	---	
C_{rss}	Reverse Transfer Capacitance		---	12.9	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	70	A
I_{SM}	Pulsed Source Current[2,5]		---	---	280	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=10A,dI/dt=100A/μs, T_J=25°C	---	103	---	nS
Q_{rr}	Reverse Recovery Charge		---	187	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

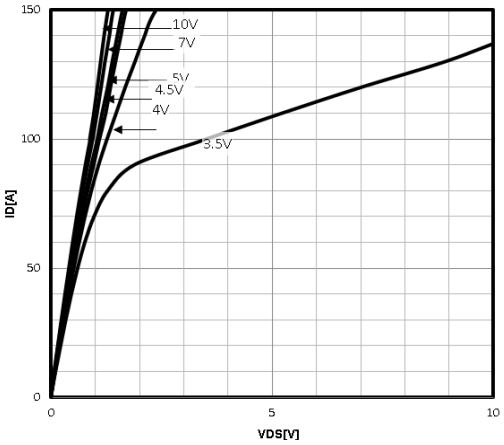
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=11A

4.The power dissipation is limited by 150℃ junction temperature

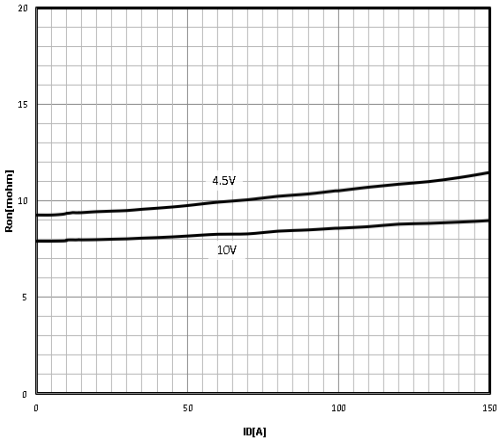
5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

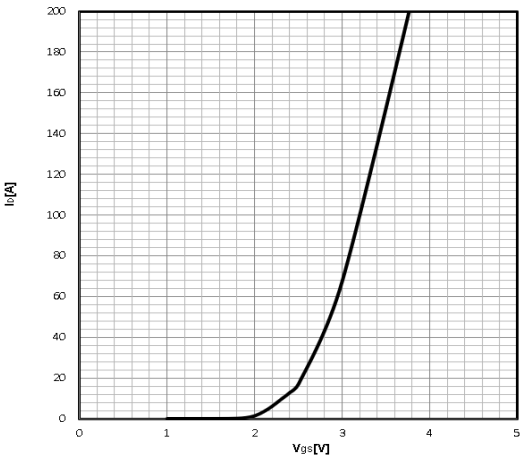
Typ. output characteristics
$I_D=f(V_{DS})$



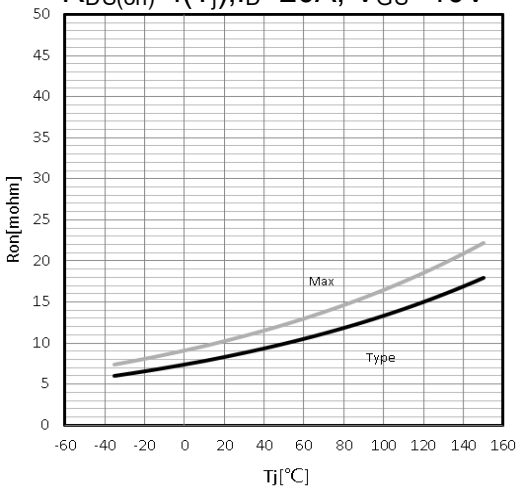
Typ. drain-source on resistance
$R_{DS(on)}=f(I_D)$



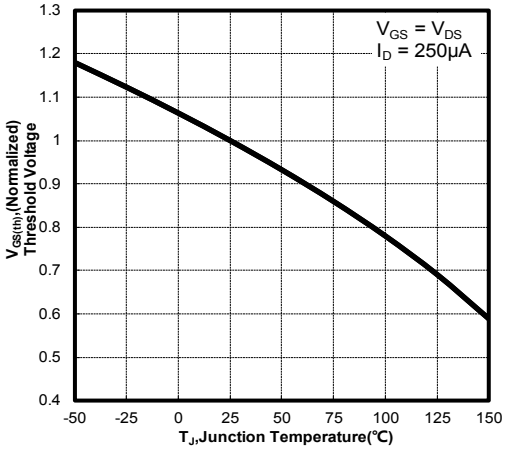
Typ. transfer characteristics
$I_D=f(V_{GS})$



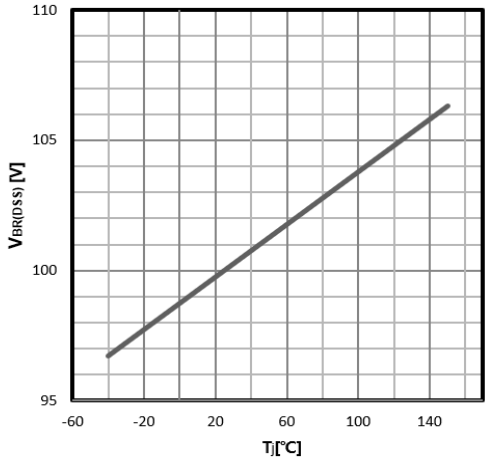
Drain-source on-state resistance
$R_{DS(on)}=f(T_j);I_D=20A;\ V_{GS}=10V$



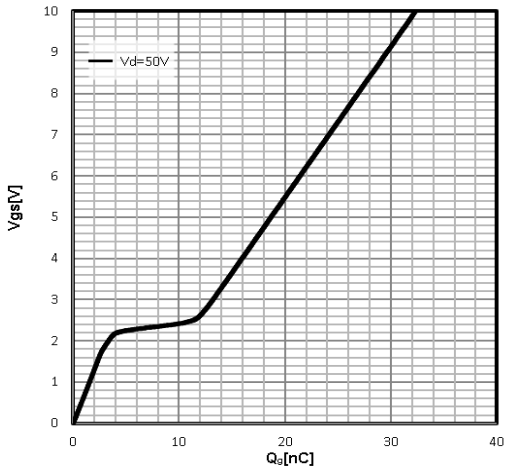
Gate Threshold Voltage
$V_{TH}=f(T_j);\ I_D=250uA$



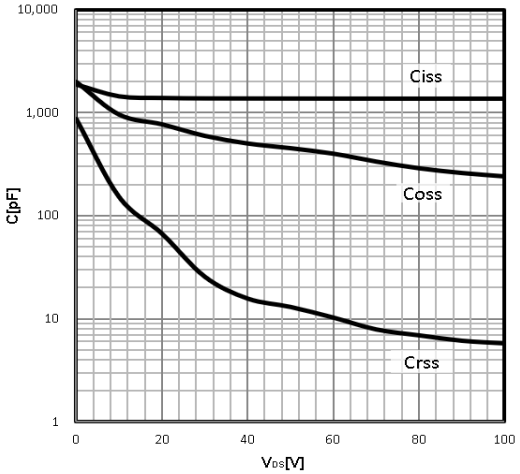
Drain-source breakdown voltage
$V_{BR(DSS)}=f(T_j);\ I_D=250uA$



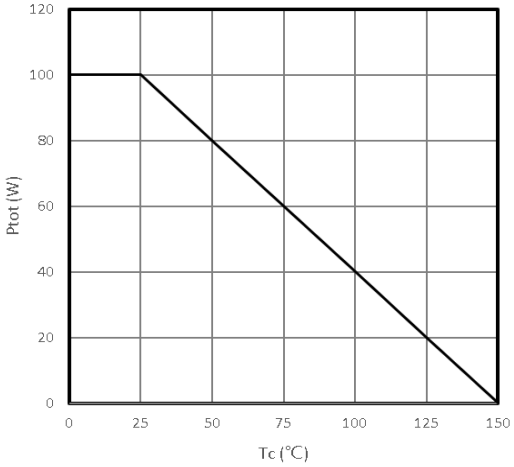
Typ. gate charge
$V_{GS}=f(Q_g)$; $I_D=10A$



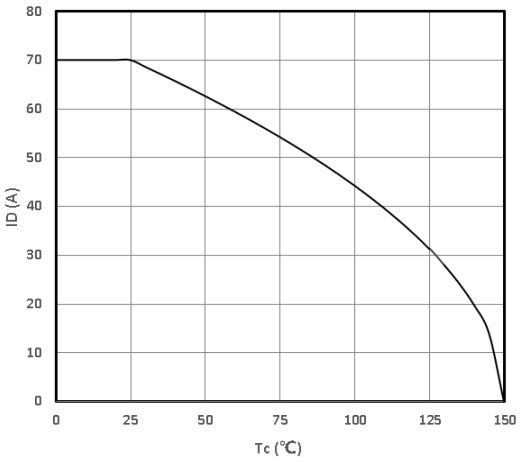
Typ. capacitances
$C=f(V_{DS})$; $V_{GS}=0V$; $f=1MHz$



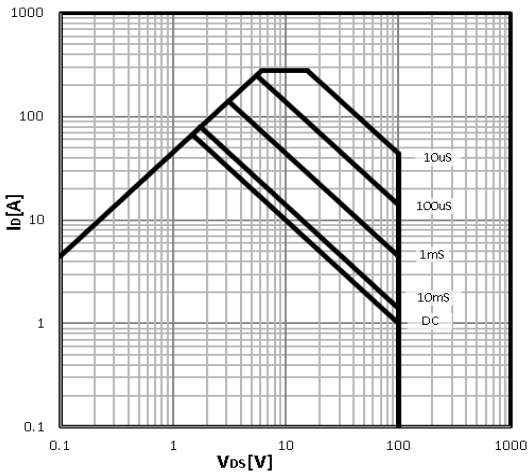
Power Dissipation
$P_{tot}=f(T_C)$



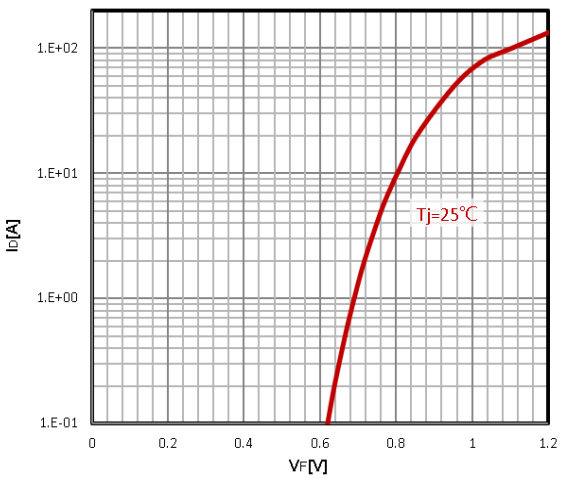
Maximum Drain Current
$I_D=f(T_C)$



Safe operating area
$I_D=f(V_{DS})$

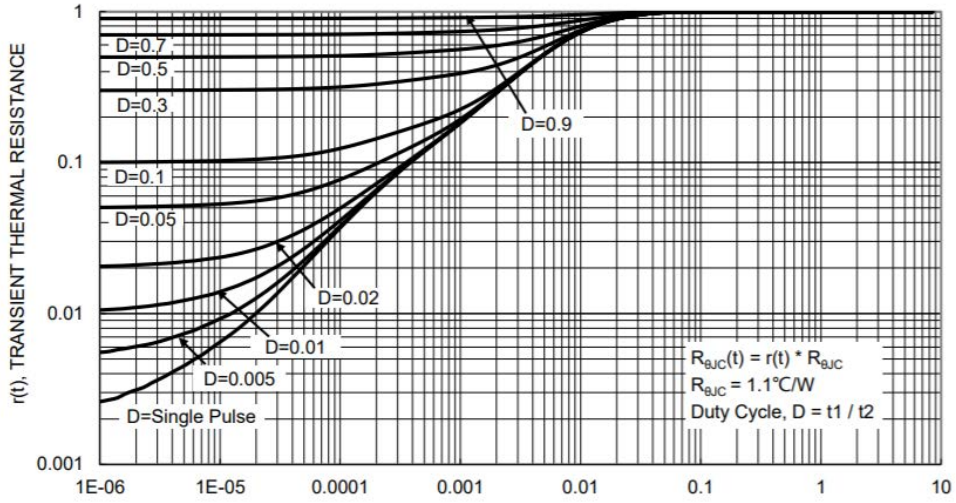


Body Diode Forward Voltage Variation
$I_F=f(V_{GS})$



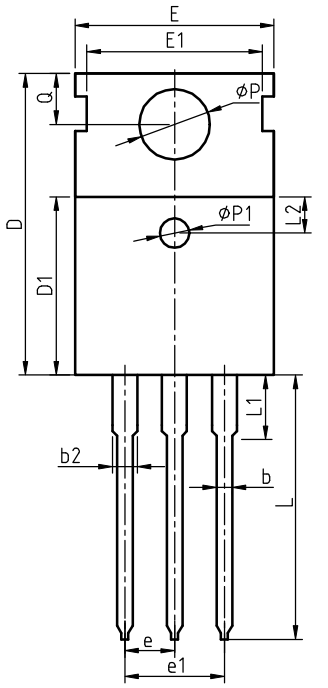
Max. transient thermal impedance

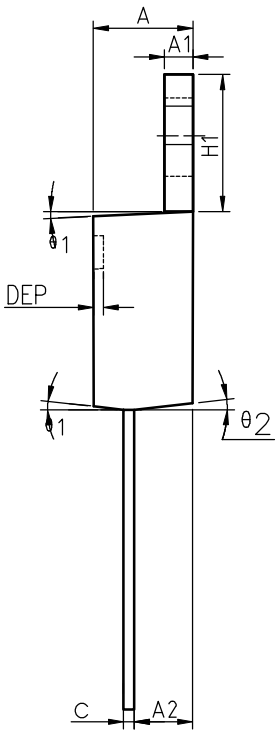
$Z_{thJC}=f(t_p)$

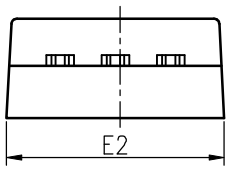


Package Information

TO-220C







COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ 1	5°	7°	9°	5°	7°	9°
θ 2	1°	3°	5°	1°	3°	5°
θ 3	1°	3°	5°	1°	3°	5°

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